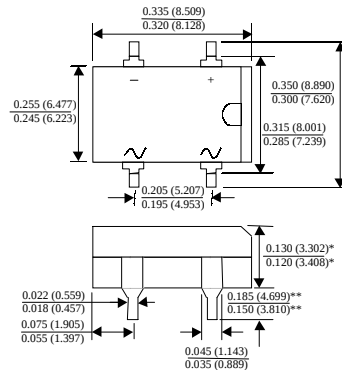


DF005M - DF10M

Features

- Surge overload rating: 50 amperes peak.
- Glass passivated junction.
- Low leakage.



LOW PROFILE ALSO AVAILABLE
BODY - - 0.102 (2.591)*
0.095 (2.413)*
LEAD - - 0.080 (2.032)**
0.050 (1.270)**

DIP

1.5 Ampere Bridge Rectifiers

Absolute Maximum Ratings*

T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
I _O	Average Rectified Current @ T _A = 40°C	1.5	A
I _{f(surge)}	Peak Forward Surge Current 8.3 ms single half-sine-wave Superimposed on rated load (JEDEC method)	50	A
P _D	Total Device Dissipation Derate above 25°C	3.1 25	W mW/°C
R _{θJA}	Thermal Resistance, Junction to Ambient,** per leg	40	°C/W
T _{stg}	Storage Temperature Range	-55 to +150	°C
T _J	Operating Junction Temperature	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

**Device mounted on PCB with 0.5 x 0.5" (13 x 13 mm).

Electrical Characteristics

T_A = 25°C unless otherwise noted

Parameter	Device							Units
	005M	01M	02M	04M	06M	08M	10M	
Peak Repetitive Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Bridge Input Voltage	35	70	140	280	420	560	700	V
DC Reverse Voltage (Rated V _R)	50	100	200	400	600	800	1000	V
Maximum Reverse Leakage, total bridge @ rated V _R T _A = 25°C T _A = 125°C	5.0 500							μA μA
Maximum Forward Voltage Drop, per bridge @ 1.0 A	1.1							V
I ² t rating for fusing t < 8.35 ms	10							A ² Sec
Typical Junction Capacitance, per leg V _R = 4.0 V, f = 1.0 MHz	25							pF

Typical Characteristics

